M **P O YYM**

- Three phase bridge and a thyristor

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T U OURU 1XO UOMX TMMO U UO (@ T_C = 25℃ unless otherwise specified)

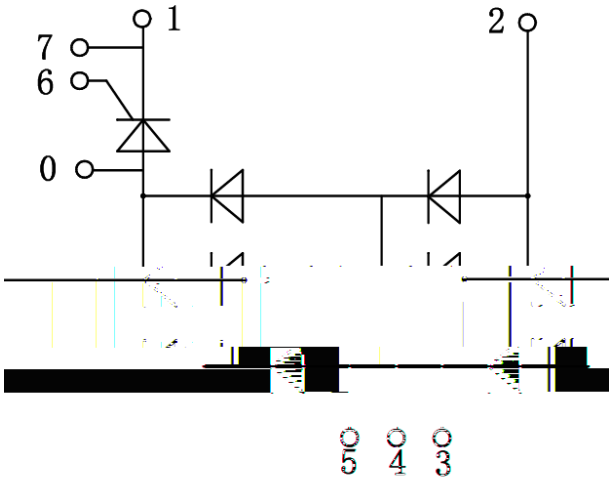
MMY	PUU	Y X	BMX			A U
			U		M	
Forward voltage	I_T=75A	V_{TM}		1.10	1.30	V
Repetitive peak off-state current	V_D = V_{DRM}, T_{vj} = 25℃	I_{DRM}			0.1	mA
	V_D = V_{DRM}, T_{vj} = 125℃				20	mA
Reverse leakage current	V_R = V_{RRM}, T_{vj} = 25℃	I_{RRM}			0.1	mA
	V_R = V_{RRM}, T_{vj} = 125℃				20	mA
Threshold voltage	For power loss calculation only T_{vj} = 125℃,	V_{TO}			0.85	V
Dynamic resistance	T_{vj} = 125℃,	r_T			2.5	mΩ
Triggering gate voltage	V_D=12V, R_L=30Ω	V_{GT}			1.8	V
Triggering gate current	V_D=12V, R_L=30Ω	I_{GT}	20		120	mA
Holding current	I_T=1A	I_H			250	mA
Latching current	I_G=1.2 IGT	I_L			300	mA
Non triggering gate voltage	V_D=V_{DRM}, T_{vj}=125℃	V_{GD}	0.25			V
Thermal resistance, junction to case	per diode	R_{thJC}			0.30	K/W
Temperature under operating conditions		T_{VjOP}	-40		125	℃

UP X MUY Y MUS (@ T_C = 25℃ unless otherwise specified)

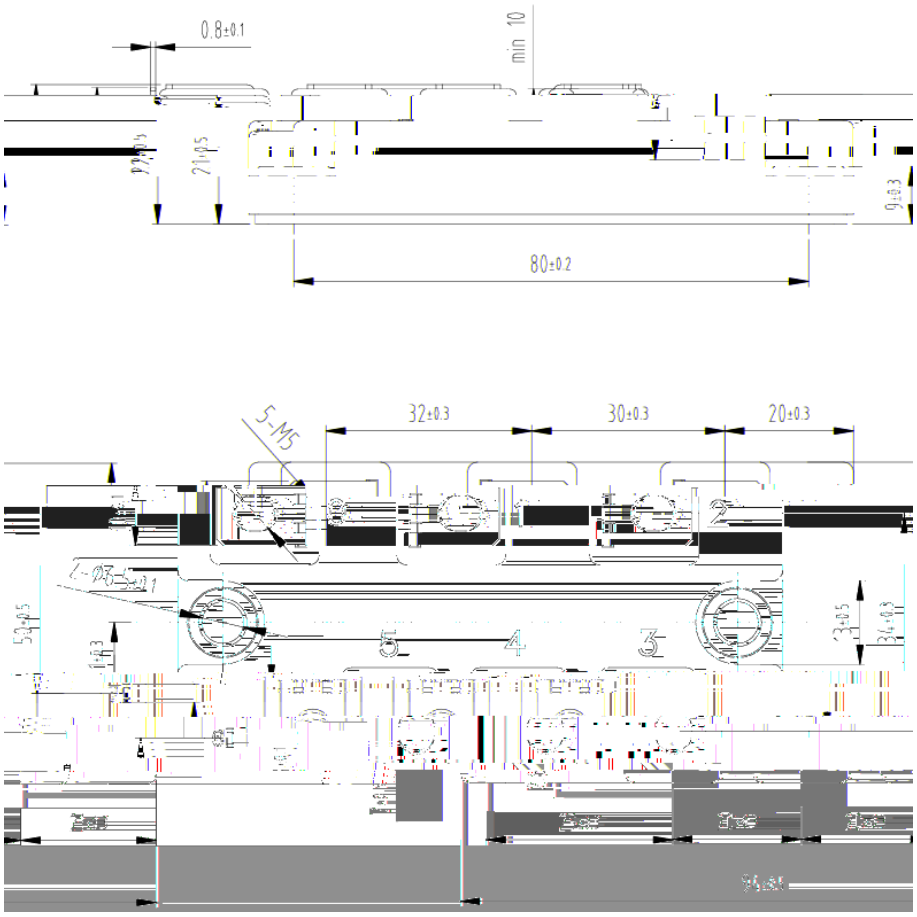
MMY	PUU	Y X	BMX	A U
Repetitive peak reverse voltage		V_{RRM}	1600	V
Non-repetitive peak reverse voltage		V_{RSM}	1700	V
Output current	T_C = 100℃	I_D	75	A
Forward surge current	1/2 cycle, Sine wave, 50Hz T_{vj} = 25℃	I_{FSM}	900	A
I^2t value for fusing		I^2t	4050	A^2s
Temperature under operating conditions		T_{VjOP}	-40 ~ +150	℃

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UO U UWS MY



MOVWS XU YY



Unit of measurement: mm

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